

ABSTRACT

A method for removing gas bubbles from a surface of a wafer is provided. Removal process is performed as the wafer surface is placed into a process solution for an electrochemical process. As the wafer surface is placed into the solution and moved towards a pressure barrier placed into the solution, a process solution flow between the wafer surface and the pressure barrier is induced to remove gas bubbles from the wafer surface. The pressure barrier includes openings which allow process solution to flow through the pressure barrier